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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Olivier RAYSSAC et al.

Confirmation No.: 5939

**Certificate**

Patent No.: 6,989,314 B2

Application No.: 10/777,721

**FEB 09 2006**

Patent Date: January 24, 2006

Filing Date: February 11, 2004

**of Correction**

For: SEMICONDUCTOR STRUCTURE  
AND METHOD OF MAKING SAME

Attorney Docket No.: 4717-10700

**REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 C.F.R. § 1.322**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Patentees hereby respectfully request the issuance of a Certificate of Correction in connection with the above-identified patent. The corrections are listed on the attached Form PTO-1050. The corrections requested are as follows:

Title page, Item (57) Abstract, lines 2, 8 and 12, change "a typical" to -- atypical --. Support for these changes appear in the abstract as filed on February 11, 2004.

The requested corrections are for errors that appear to have been made by the Office. Therefore, no fee is believed to be due for this request. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814. Please issue a Certificate of Correction in due course.

Respectfully submitted,

2-6-06

Date

Allan A. Fanucci, Reg. No. 30,256

**WINSTON & STRAWN LLP**  
**Customer No. 28765**

212-294-3311

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**UNITED STATES PATENT AND TRADEMARK OFFICE**  
**CERTIFICATE OF CORRECTION**

PATENT NO.: 6,989,314 B2  
DATED: January 24, 2006  
INVENTORS: Rayssac et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:

Item (57) Abstract, lines 2, 8 and 12, change "a typical" to -- a typical --.



US006989314B2

(12) **United States Patent**  
Rayssac et al.

(10) **Patent No.:** US 6,989,314 B2  
(45) **Date of Patent:** Jan. 24, 2006

(54) **SEMICONDUCTOR STRUCTURE AND METHOD OF MAKING SAME**

(75) **Inventors:** Olivier Rayssac, Grenoble (FR);  
Muriel Martinez, St. Egreve (FR);  
Sephora Blisson, Grenoble (FR);  
Lionel Portigliatti, Seyssin (FR)

(73) **Assignee:** S.O.I.Tec Silicon on Insulator Technologies S.A., Bernin (FR)

(\*) **Notice:** Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) **Appl. No.:** 10/777,721

(22) **Filed:** Feb. 11, 2004

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(51) **Int. Cl.**  
H01L 21/76 (2006.01)  
H01L 21/30 (2006.01)  
H01L 21/46 (2006.01)  
(52) **U.S. Cl.** ..... 438/406; 438/455; 438/456  
(58) **Field of Classification Search** ..... 438/288,  
438/406, 455, 458, 689, 118, 409, 456, 974  
See application file for complete search history.

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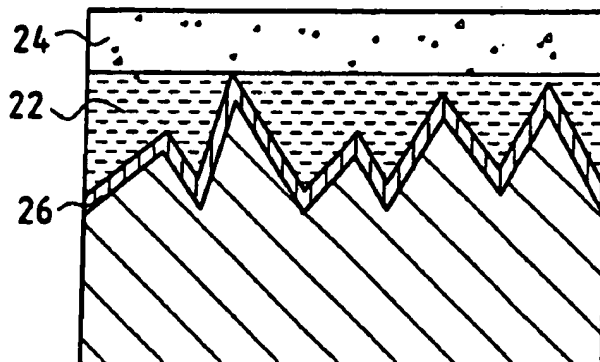
*Primary Examiner*—Walter L. Lindsay, Jr.  
(74) *Attorney, Agent, or Firm*—Winston & Strawn LLP

(57) **ABSTRACT**

A semiconductor structure includes a substrate having a surface and being made of a material that provides a typical surface properties to the surface, a bonding layer on the surface of the substrate, and a further layer molecularly bonded to the bonding layer. A method for fabricating such a semiconductor structure includes providing a substrate having a surface and being made of a material that provides a typical surface properties to the surface, providing a bonding layer on the surface of the substrate, smoothing the bonding layer to provide a surface that is capable of molecular bonding, and molecularly bonding a further layer to the bonding layer to form the structure. The typical surface properties preferably include at least one of a roughness of more than 0.5 nm rms, or a roughness of at least 0.4 nm rms that is difficult to polish, or a chemical composition that is incompatible with molecular bonding.

atypical

23 Claims, 3 Drawing Sheets



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